

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A sputtering target consisting essentially of Si, wherein a ratio ($I_{(111)}/I_{(220)}$) of peak intensity ($I_{(111)}$) of (111) face to peak intensity ($I_{(220)}$) of (220) face of Si is in a range of 1.8 ± 0.3 when a sputtering surface of the target is measured for crystal face orientation by X-ray diffractometry.
2. (Original) The sputtering target according to claim 1, comprising an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
3. (Original) The sputtering target according to claim 1, having hardness in a range of Hv 300 or more and Hv 800 or less in terms of Vickers hardness.
4. (Original) A sputtering target consisting essentially of Si, wherein the target comprises an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
5. (Original) A sputtering target consisting essentially of Si, wherein the target has hardness in a range of Hv 300 or more and Hv 800 or less in terms of Vickers hardness.
6. (Original) The sputtering target according to claim 5, wherein the target as a whole has dispersion of the Vickers hardness within 30 %.
7. (Original) The sputtering target according to claim 5, comprising an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
8. (Original) A sputtering target consisting essentially of Si, wherein an oxygen content of the target is in a range of 0.01 mass% or more and 1 mass% or less.

9. (Original) The sputtering target according to claim 8, comprising an Si sintered material having a relative density in a range of 70 % or more and 95 % or less.
10. (Currently amended) The sputtering target according to ~~any one of claims 1 through 9~~ claim 1, which is a target for forming an oxide film.
11. (Currently amended) The sputtering target according to ~~any one of claims 1 through 10~~ claim 1, which is used as a target for forming an optical thin film.
12. (Currently amended) A process for producing an Si oxide film, comprising forming an Si oxide film by sputtering the sputtering target according to ~~any one of claims 1 through 9~~ claim 1 in an oxygen-containing atmosphere.
13. (Original) The process for producing an Si oxide film according to claim 12, wherein the Si oxide film is an optical thin film.